

Attenuated UV photodiode

Model GT-UVV-LWD

General Features:

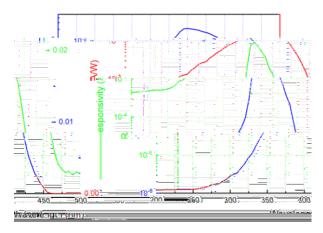
- Indium gallium nitride based material
- Photovoltaic mode operation
- TO-46 metal housing with in-situ attenuator
- Long lifetime for strong UV radiation testing applications



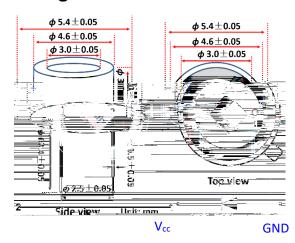
Specifications:

Parameters	Symbol	Value	Unit
Maximum ratings			
Operation temperature range	T _{opt}	-25-85	°C
Storage temperature range	T _{sto}	-40-85	°C
Soldering temperature (3 s)	T _{sol}	260	°C
Reverse voltage	V_{r-max}	-10	V
General characteristics (25 °C)			
Chip size	А	1	mm²
Dark current (V _r = -1 V)	I _d	<1	nA
Temperature coefficient	T _c	0.05	%/°C
Capacitance (at 0 V and 1 MHz)	C_p	60	pF
Spectral response characteristics (25 °C)			
Wavelength of peak responsivity	р	375	nm
Peak responsivity (at 375 nm)	R _{max}	0.021	A/W
Spectral response range (R=0.1×R _{max})	-	290-440	nm
UV-visible rejection ratio (R _{max} /R _{460 nm})	-	>104	-

Spectral response



Package dimensions





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Application circuit:

Evaluation circuit board:

A small multifunctional amplifier board for developers to simplify and support application development can be separately provided. The evaluation board with one amplifier channel supports both SMD- and TO-type packaged UV photodiodes supplied by GaNo Opto. Users could select one of the two mounting ports for UV photodiode evaluation, while both ports should not be used at the same time.

The evaluation board supports measurement range adjustment function via a dip switch. Different setting of the dip switch corresponds to different load resistance value, which determines the amplification magnitude of the signal processing circuit. A temperature sensor on board is used for embedded temperature compensation.

The UV photodiode evaluation board has both analog and digital output interface. Analog